

APPARATUS AND METHOD FOR CONTROLLING FILM THICKNESS IN A CHEMICAL MECHANICAL PLANARIZATION SYSTEM

ABSTRACT OF THE DISCLOSURE

An apparatus for use in a chemical mechanical planarization (CMP) system is provided. A head capable of being positioned at a proximate location over a polishing pad includes an input and an output defined in the head. The input is capable of delivering a fluid at the proximate location on the surface of a polishing pad. The output being oriented adjacent to the input is capable of removing at least part of the fluid delivered onto the surface of the polishing pad. A method for controlling properties of a film over a polishing pad surface is also provided.